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APPLICATION NO. FILING DATE FIRST NAMED INVENTOR ATTORNEY DOCKET NO. CONFIRMATION NO. 10/757,638 01/13/2004 Weimin Li MICRON.140DV1C1 20995 7590 12/13/2004 **EXAMINER** KNOBBE MARTENS OLSON & BEAR LLP LUHRS, MICHAEL K 2040 MAIN STREET ART UNIT PAPER NUMBER FOURTEENTH FLOOR IRVINE, CA 92614 2824

DATE MAILED: 12/13/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
• •	10/757,638	LI ET AL.		
Office Action Summary	Examiner	Art Unit		
	Michael K. Luhrs	2824		
The MAILING DATE of this communication app				
Period for Reply				
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl If NO period for reply is specified above, the maximum statutory period or - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tim y within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	ely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).		
Status				
1)⊠ Responsive to communication(s) filed on <u>02 N</u>	ovember 2004.			
<u> </u>	action is non-final.			
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is				
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims				
4)⊠ Claim(s) <u>1-7,9 and 10</u> is/are pending in the application.				
• • • • • • • • • • • • • • • • • • • •	4a) Of the above claim(s) is/are withdrawn from consideration.			
5) Claim(s) is/are allowed.				
6)⊠ Claim(s) <u>1-7,9 and 10</u> is/are rejected.				
7) Claim(s) is/are objected to.				
8) Claim(s) are subject to restriction and/o	r election requirement.			
Application Papers				
9) The specification is objected to by the Examine	er.			
10)⊠ The drawing(s) filed on <u>13 January 2004</u> is/are: a)⊠ accepted or b)□ objected to by the Examiner.				
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).				
11) The oath or declaration is objected to by the Ex	caminer. Note the attached Office	Action or form PTO-152.		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(a)	-(d) or (f).		
a) ☐ All b) ☐ Some * c) ☐ None of:				
1. Certified copies of the priority documents have been received.				
2. Certified copies of the priority document	s have been received in Application	on No		
Copies of the certified copies of the prio	rity documents have been receive	d in this National Stage		
application from the International Burea	, , ,			
* See the attached detailed Office action for a list	of the certified copies not receive	d.		
Attachment(s)				
1) Notice of References Cited (PTO-892)	4) Interview Summary			
 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) 	Paper No(s)/Mail Da	te atent Application (PTO-152)		
Paper No(s)/Mail Date	6) Other: <u>search histor</u>			

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DETAILED ACTION

Claim Objections

1. Claim 1 is objected to because of the following informalities: claim 1, step (viii) replace "conductive" with —platinum—to match the "platinum" precursor gas (antecedent) in steps (ii) and (vii). Appropriate correction is required.

Double Patenting

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

3. Claims 1-7, 9 and 10 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims {1,3, 12} and 4, 5, 8, 9, 10, 11, 13, 14 of U.S. Patent No. 6,576,538. Although the conflicting claims are not identical, they are not patentably distinct from each other because they claim similar subject matter. The chart below shows claims {1, 3, 12} of '538 as they compare to claim 1 of the present application. It can be seen that the present application having the **platinum** precursor gas is of the same subject as '538 claim 1 conductive precursor gas (i.e. platinum is conductive) as further seen in '538 claim 3 <u>is a platinum</u> precursor gas. And the "halting" occurs in claim 12 of '538.

'538	Present application	
1. A method of forming a conductive layer on a semiconductor device, the method comprising:	(Currently Amended) A method of forming a platinum conductive layer on a semiconductor device, the method comprising;	
(i) positioning a semiconductor device within a chemical vapor deposition chamber;	(i) positioning the semiconductor device within a chemical vapor deposition chamber;	
(ii) introducing a conductive	(ii) introducing a platinum precursor	

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precursor gas into the chemical vapor	gas into the chemical vapor deposition
deposition chamber for a first period	chamber for a first period of time so
of time;	as to deposit a platinum conductive
	layer on the device;
(ii) (sic) introducing a reactant	(iii) introducing a reactant into the
into the chemical vapor deposition	chemical vapor deposition chamber for
chamber for a second period of time,	a second period of time, so that
so that the conductive layer is	organic waste compounds contacting the
formed on the semiconductor device	platinum conductive layer are removed
and organic waste compounds	to thereby facilitate subsequent
positioned within and on the	deposition of the platinum conductive layer; and
conductive layer of the first thickness are removed;	conductive layer; and
(iv) monitoring the rate of	See (v) (vi) and (vii) below
deposition of the conductive layer,	See (V) (VI) and (VII) below
wherein the supply of conductive	
precursor gas is halted upon	•
determining when the rate of	
deposition is less than a desired	
threshold; and	
(v) continuing acts (ii), (iii), and	(iv) continuing acts (ii) and (iii)
(iv) until the conductive layer of a	until the conductive layer of a
desired thickness is achieved.	desired thickness is achieved)
	(v) monitoring the rate of deposition
	of the platinum layer:
	(vi) determining when the rate of
	deposition has decreased below a desired threshold;
	(vii) halting the supply of platinum
	precursor gas upon determining that
	the rate of deposition is less than
	the desired threshold: and
3. The method of claim 1, wherein	
introducing the conductive precursor	
gas into the chemical vapor	
deposition chamber comprises	
introducing a platinum precursor gas	
into the chemical vapor deposition	
chamber.	
12. The method of claim 1, further	(viii) providing the reactant after
comprising: providing only the	halting the supply of the conductive
reactant after halting the supply of	(sic) -platinum-precursor gas.
the conductive precursor gas.	(and, broadfact 200.

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4. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action.

Accordingly, THIS ACTION IS MADE FINAL. See MPEP § 706.07(a). Applicant is reminded of the extension

of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the

mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final

action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period,

then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee

pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however,

will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

5. Any inquiry concerning this communication or earlier communications from the examiner should be

directed to Michael K. Luhrs whose telephone number is 571-272-1874. The examiner can normally be reached on

M-F, 8-5.

6. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard T.

Elms can be reached on 571-272-1869. The fax phone number for the organization where this application or

proceeding is assigned is 703-872-9306.

7. Information regarding the status of an application may be obtained from the Patent Application Information

Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR

or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more

information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the

Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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